

SMT970

High Performance Infrared TOP IR LED

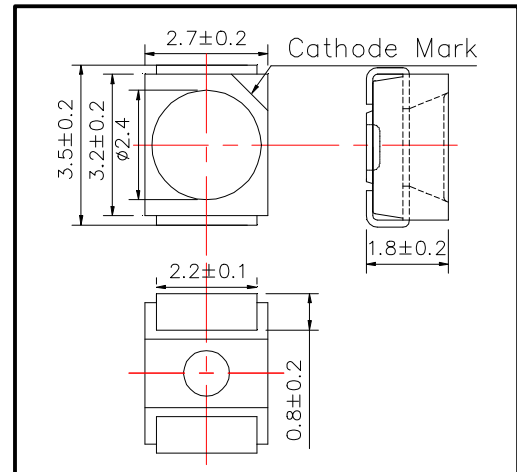
SMT970 consists of a GaAs LED mounted on the lead frame as TOP LED package and is 4mW typical of output power.

It emits a spectral band of radiation at 970nm.

Specifications

- 1) Product Name TOP IR LED
- 2) Type No. SMT970
- 3) Chip
 - (1) Chip Material GaAs
 - (2) Peak Wavelength 970nm typ.
- 4) Package
 - (1) Lead Frame Die Silver Plated
 - (2) Package Resin PPA Resin
 - (3) Lens Epoxy Resin

Outer dimension(Unit:mm)



Absolute Maximum Rating

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	140	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	500	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-20 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +800	°C	
Soldering Temperature	T _{SOL}	240	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 230°C

Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA		1.30	1.45	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =50mA	2.0	4.0		mW
Radiant Intensity	I _E	I _F =50mA		1.5		mW/sr
Peak Wavelength	λ _P	I _F =50mA	960	970	980	nm
Half Width	Δλ	I _F =50mA		50		nm
Viewing Half Angle	Q _{1/2}	I _F =50mA		±55		deg.
Rise Time	t _r	I _F =50mA		1000		ns
Fall Time	t _f	I _F =50mA		500		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.